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(54) Title: AN ELECTRICALLY CONDUCTING STRUCTURE FOR A LIGHT TRANSMISSIBLE DEVICE

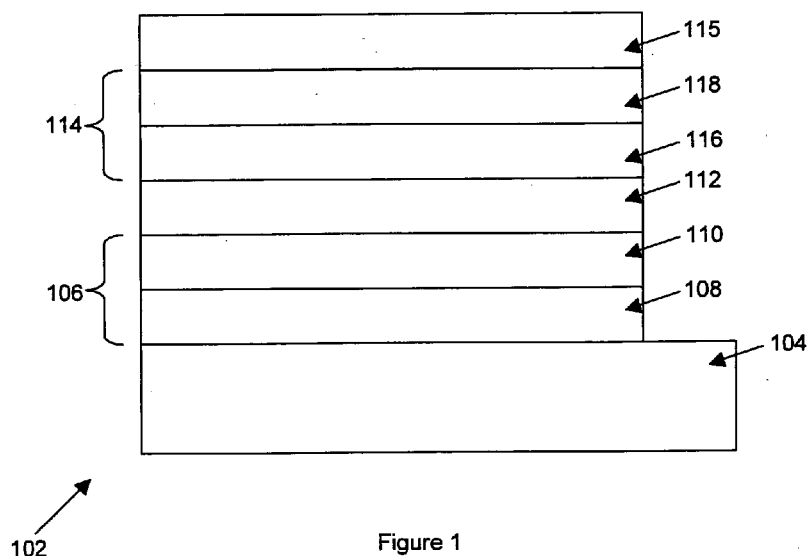


Figure 1

(57) Abstract: An electrically conducting structure for a light transmissible device and a method of forming an electrically conducting structure for a light transmissible device are provided. The structure comprises a first transparent conducting material layer formed using first process conditions; at least one other transparent conducting material layer formed directly on the first layer, said at least one other transparent conducting material layer being formed using second process conditions that are different from the first process conditions; and wherein the first layer functions as a buffer layer to reduce adverse effects for the light transmissible device during formation of said at least one other transparent conducting material layer.